

1754

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY
APPLICANTS

Atty. Docket No. (Opt.)
FOC1100-1



Applicant
Robert Jackson

Application Number
10/038,745

Filed
January 2, 2002

For: Method and System for On-Site Generation
and Distribution of a Process Gas

Certification Under 37 C.F.R. §1.8

I hereby certify that this document is being deposited
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Mail in an envelope addressed to: Commissioner for
Patents, P.O. Box 1450, Alexandria, VA 22312-1450 on
October 31, 2003.

Carolyn J. Williams
Carolyn J. Williams

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INFORMATION DISCLOSURE STATEMENT

Applicant respectfully requests, pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, that the art listed on the attached PTO/SB/08A and PTO/SB/08B forms be considered and cited in the examination of the above-identified application. A copy of the art is enclosed for the convenience of the Examiner.

Furthermore, pursuant to 37 C.F.R. §§ 1.97(g) and (h), no representation is made that a search has been made or that this art is material to patentability of the present application. Applicant respectfully submits that the claims of Applicant's above-referenced patent is patentably distinguishable from these references.

Applicant believes no fee is due at this time. However, the Commissioner is hereby authorized to charge any fees due, or refund any credit, to Deposit Account No. 50-0456 of Gray Cary Ware & Freidenrich LLP for any fee under 37 C.F.R. §1.17(i).

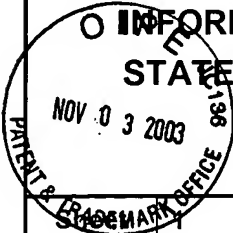
Respectfully submitted,

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Attorneys for Applicant

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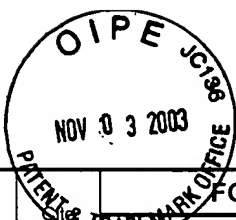
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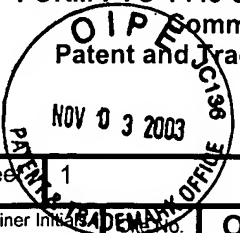
		Application Number	10/038,745
		Filing Date	January 2, 2002
		First Named Inventor	Robert Jackson
		Group Art Unit	1754
		Examiner Name	Ngoc Nguyen
OF 1		Attorney Docket Number	FCC1100-1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear
		Number	Kind Code (if known)			
	A1	4,818,326		04/04/89	Liu, et al.	
	A2	4,988,533		01/29/91	Freeman et al.	
	A3	5,129,958		07/14/92	Nagashima et al.	
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	A5	5,449,411		09/12/95	Fukuda et al.	
	A6	5,620,526		04/15/97	Watatani et al.	
	A7	5,679,215		10/21/97	Barnes, et al.	
	A8	5,693,147		12/02/97	Ward, et al.	
	A9	5,814,562		09/29/93	Green et al.	
	A10	5,824,375		10/20/98	Gupta	
	A11	5,824,607		10/20/98	Trow et al.	
	A12	6,070,599		06/06/00	Ghanayem et al.	
	A13	6,174,373	B1	01/16/01	Ghanayem et al.	
	A14	6,286,451	B1	09/11/01	Ishikawa et al.	
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	A21	6,569,257	B1	05/27/03	Nguyen et al.	
	A22	6,599,574	B1	07/29/03	Yieh et al.	
	A23	2003/0010354	A1	01/16/03	Goto et al.	
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	No.	Country Code	Number	Kind Code (if known)			
	B1	WO 99/12196 ✓		A1	03/11/99	Applied Materials, Inc.	
	B2	JP08017804 ✓			01/19/96	Sony Corp.	
	B3	EP 0 819 780 ✓		A2	01/21/98	Applied Materials, Inc.	
Examiner Signature					Date Considered		

FORM PTO 1449 US Department of Commerce Patent and Trademark Office 		Application Number	10/038,745
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		First Named Inventor	Robert Jackson
		Group Art Unit	1754
		Examiner Name	Ngoc Nguyen
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Examiner Initials	OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS		Date
C1	International Sematech, "Motorola Evaluation of the Applied Science and Technology, Inc. (ASTeX) Astron Technology for Perfluorocompound (PFC) Emissions Reductions on the Applied Materials DxL Chemical Vapor Deposition (CVD) Chamber."	April 16, 1999	
C2	Sobolev, "Improvement of a Chemical Sensor for Detection of Hydrogen Fluoride in Gaseous Environment and a Fluoride Generator for its Calibration," http://www.tech-db.ru/istc/db/ptra.nsf/we/1204 , 4 pages.	March 2003	
C3	Astron, "Reactive Gas Generators," MKS Instruments, Inc., 4 pages.		
C4	Chen, et al, "Advances in Remote Plasma Sources for Cleaning 300 mm and Flat Panel CVD Systems, Semiconductor Magazine."	August 2003	
C5	Kranefuss, "Etching System," IBM Technical Disclosure Bulletin, Vol. 9, No. 8, pg. 2956.	January 1977	
C6	"Anisotropic and Selective Etching of Tungsten Silicide-Tungsten-Tungsten Silicide Composite Stack," IBM Technical Disclosure Bulletin, Vol. 29, No. 3., pg. 1151.	August 1986	
C7	Bergendahl, et al., "Positive Photoresist for Permeation Etching," IBM Technical Disclosure Bulletin, Vol. 23, No. 10, pg. 4446.	March 1981	
C8	Flamm et al., "Reaction of Fluorine Atoms with SiO ₂ ," J. Appl. Phys., 50 (10), pages 6211-3,	October 1980	
C9	Donnelly et al., "Studies of Chemiluminescence Accompanying Fluorine Atom Etching of Silicon," J. Appl. Phys., 51 (10), pages 5273-6.	October 1980	
C10	Flamm et al., "The Reaction of Fluorine Atoms with Silicon," J. Appl. Phys., 52 (5), pages 3633-9.	May 1981	
C11	Mucha et al., "Chemiluminescence and the Reaction of Molecular Fluorine with Silicon," J. Phys. Chem., Vol. 85, Pages 3529-3532.	1981	
C12	Mucha et al., "Chemiluminescent Reaction of SiF ₂ with Fluorine and the Etching of Silicon by Atomic and Molecular Fluorine," (6), Pages 4553-4, J. Appl. Phys., 53(6).	June 1982	
C13	Flamm et al., "XeF ₂ and F-atom Reactions with Si: Their Significance for Plasma Etching," Solid State Technology, Pages 117-121.	April 1983	
C14	Merriam-Webster's Collegiate Dictionary, Tenth Edition, page 746.		